

IN THE SPECIFICATION:

Please amend the specification as follows:

Please amend the paragraphs on pages 31 and 32, from line 4 on page 31 to line 26 on page 32, as follows:

A high-frequency element mounting substrate shown in Fig. 7A is manufactured using a dielectric substrate 901 made from an aluminum nitride material. A mounted portion 931 of the optical modulator is configured in the same manner as that described in the first embodiment. A point of difference between this configuration and the first embodiment is that a semiconductor laser mounted portion 932 is formed on the same dielectric substrate 901. As is the case with the optical modulator mounted portion 931, it has an index marker for positioning 910. In addition, a laser mounting electrode portion 908 and a laser driving electrode portion 909 are formed. For the purpose of reducing light reflection between end faces of optical elements described below, a portion on which an optical modulator and a semiconductor laser are mounted has a slanting mount structure of 7 degrees. In this connection, in Fig. 7A, reference numeral 902 is a high-frequency line; reference numeral 903 is a terminal thin film resistance; reference numeral 904 is gold tin solder; reference numeral 905 is a ground line; reference numeral 906 is a ground via hole; reference numeral 907 is gold tin solder; reference numeral 908 ~~numeral~~ 908 is gold tin solder; reference numeral 909 is a laser driving electrode terminal; reference numeral 910 is an index marker for positioning; reference numeral 911 is gold tin solder; reference numeral 931 is an optical modulator mounted portion; and reference numeral 932 is a semiconductor laser mounted portion.

An optical modulator 971 shown in Fig. 7B has a configuration similar to the optical modulator in the first embodiment, and is formed on a semi-insulating GaAs substrate 960. A semiconductor laser 972 shown in the figure is formed on a n-type InP substrate. The semiconductor laser 972 is a multi-quantum well distributed feedback laser made from an InGaAsP material, which has an operation wavelength band of 1.55 μm , and which has a built-in diffraction grating 953. For the purpose of improving efficiency in optical coupling between the optical ~~modulators~~ modulator 971 and the semiconductor laser 972, input and output edges of both are provided with a beam-expanded optical waveguide

965. In Fig. 7B, reference numeral 952 is a n-type InP substrate; reference numeral 953 is a diffraction grating; reference numeral 954 is a p-type electrode; reference numeral 955
~~numeral 955~~ is a n-type electrode; a reference numeral 960 is a semi-insulating GaAs substrate; reference numeral 961 is a multiplexer or a branching filter; reference numeral 962 is separated electrodes for modulator; reference numeral 963 is a ground line on optical modulator side; and reference numeral 964 is an index marker for positioning.